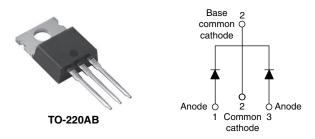


Vishay Semiconductors

Schottky Rectifier, 2 x 15 A



PRODUCT SUMMARY				
Package	TO-220AB			
I _{F(AV)}	2 x 15 A			
V _R	45 V			
V _F at I _F	See Electrical table			
I _{RM} max.	100 mA at 125 °C			
T _J max.	150 °C			
Diode variation	Common cathode			
E _{AS}	10 mJ			

FEATURES

- 150 °C T_J operation
- Low forward voltage drop
- High frequency operation
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- Guard ring for enhanced ruggedness and long term reliability
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified according to JEDEC-JESD47
- Halogen-free according to IEC 61249-2-21 definition (-N3 only)

DESCRIPTION

This center tap Schottky rectifier has been optimized for low reverse leakage at high temperature. The proprietary barrier technology allows for reliable operation up to 150 °C junction temperature. Typical applications are in switching power supplies, converters, freewheeling diodes, and reverse battery protection.

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	UNITS					
I _{F(AV)}	Rectangular waveform (per device)	30	А			
V _{RRM}		35/45	V			
I _{FRM}	$T_{\rm C} = 123 \ ^{\circ}{\rm C}$ (per leg)	30	٨			
I _{FSM}	t _p = 5 μs sine	1020	A			
V _F	20 A _{pk} , T _J = 125 °C	0.6	V			
TJ	Range	- 65 to 150	°C			

VOLTAGE RATINGS						
PARAMETER SYMBOL VS-MBR3045CTPbF VS-MBR3045CT-N3 UNITS						
Maximum DC reverse voltage	V _R	45	45	M		
Maximum working peak reverse voltage	V _{RWM}	40	40	v		

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	PARAMETER SYMBOL TEST CONDITIONS		VALUES	UNITS			
Maximum average	per leg		15 100 °C metad V				
forward current	per device	I _{F(AV)}	$T_{C} = 123 \text{ °C}, \text{ rated } V_{R}$		30		
Peak repetitive forward curre	ent per leg	I _{FRM}	Rated V _R , square wave, 20 kHz, T _C = 123 °C		30		
Non-repetitive peak surge current		I _{FSM}	5 μs sine or 3 μs rect. pulse	Following any rated load condition and with rated V _{RRM} applied	1020	A	
			Surge applied at rated load conditions halfwave, single phase, 60 Hz		200		
Non-repetitive avalanche en	ergy per leg	E _{AS}	T _J = 25 °C, I _{AS} = 2 A, L = 5 mH		10	mJ	
Repetitive avalanche current	per leg	I _{AR}	Current decaying linearly to zero in 1 μs Frequency limited by T_J maximum V_A = 1.5 x V_R typical		2	А	

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1



RoHS

COMPLIANT

HALOGEN

FREE



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ELECTRICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONE	DITIONS	VALUES	UNITS	
		30 A	T _J = 25 °C	0.76		
Maximum forward voltage drop	V _{FM} ⁽¹⁾	20 A	T,I = 125 °C	0.6	V	
		30 A	1j = 125 C	0.72		
Maximum instantaneous reverse current	I _{RM} ⁽¹⁾	T _J = 25 °C	Rated DC voltage	1	mA	
		T _J = 125 °C	Haleu DC Vollage	100		
Threshold voltage	V _{F(TO)}	$T_{i} = T_{i}$ maximum		0.29	V	
Forward slope resistance	r _t	ij – ij maximum		13.6	mΩ	
Maximum junction capacitance	CT	V_{R} = 5 V_{DC} (test signal range 100 kHz to 1 MHz) 25 °C		800	pF	
Typical series inductance	L _S	Measured from top of terminal to mounting plane		8.0	nH	
Maximum voltage rate of change	dV/dt	Rated V _R		10 000	V/µs	

Note

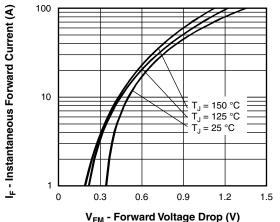
⁽¹⁾ Pulse width < 300 μ s, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS		
Maximum junction temperature range	TJ		- 65 to 150	٥°		
Maximum storage temperature range	T _{Stg}		- 65 to 175			
Maximum thermal resistance, junction to case per leg	R _{thJC}	DC operation	1.5			
Typical thermal resistance, case to heatsink	R _{thCS}	Mounting surface, smooth and greased Only for TO-220	ed 0.50			
Maximum thermal resistance, junction to ambient	R _{thJA}	DC operation For D ² PAK and TO-262	50			
Approximate weight			2	g		
Approximate weight			0.07	0Z.		
Mounting torque	1	Non-lubricated threads	6 (5)	kgf · cm		
Mounting torque maximum	ı	Non-Iudricated trifeads	12 (10)	(lbf ⋅ in)		
Marking device		Case style TO-220AB	MBR3045CT			

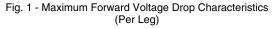
2



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 v_{FM} - Forward voltage Drop (v)



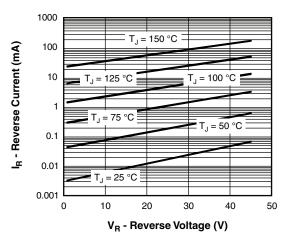


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage (Per Leg)

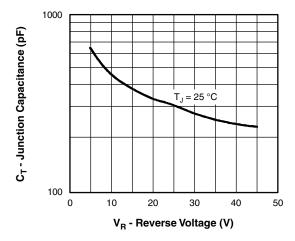


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

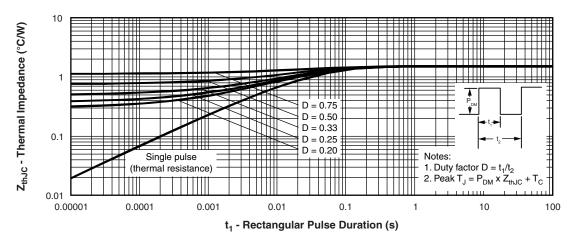
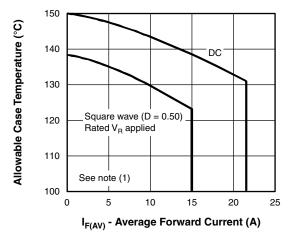


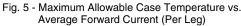
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Leg)

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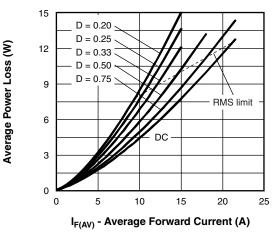


Fig. 6 - Forward Power Loss Characteristics (Per Leg)

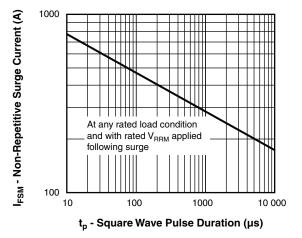


Fig. 7 - Maximum Non-Repetitive Surge Current (Per Leg)

Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
 - $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$



Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code

e	VS-	MBR	30	45	СТ	PbF
	1	2	3	4	5	6

- 1 Vishay Semiconductors product
- 2 Schottky MBR series
 - Current rating (30 = 30 A)
 - Voltage ratings (045 = 45 V)
 - CT = Essential part number
 - Environmental digit

- PbF = Lead (Pb)-free and RoHS compliant
- -N3 = Halogen-free, RoHS compliant, and totally lead (Pb)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION							
VS-MBR3045CTPbF	50	1000	Antistatic plastic tube				
VS-MBR3045CT-N3	50	1000	Antistatic plastic tube				

LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
	TO-220AB PbF	www.vishay.com/doc?95225			
Part marking information	TO-220AB -N3	www.vishay.com/doc?95028			



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches





.ead	assignments

Diodes

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STWBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- ⁽²⁾ Lead dimension and finish uncontrolled in L1
- ⁽³⁾ Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left(4\right) }$ Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

MILLIMETERS INCHES SYMBOL NOTES MIN. MAX. MIN. MAX. 10.51 0.414 10.11 0.398 3,6 Е E1 6.86 8.89 0.270 0.350 6 E2 0.76 0.030 7 --2.41 2.67 0.095 0.105 е 0.208 e1 4.88 5.28 0.192 H1 6.09 6.48 0.240 0.255 6,7 13.52 14.02 0.532 0.552 L L1 3.32 3.82 0.131 0.150 2 ØΡ 3.54 3.73 0.139 0.147 2.60 0.102 Q 3.00 0.118 90° to 93° 90° to 93° θ

Conforms to JEDEC outline TO-220AB

- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline



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